

IN THE CLAIMS

1. **(original)** A method of forming a semiconductor thin-film, comprising:

 irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region;

and

 irradiating a second laser beam to the thin-film in such a way as not to overlap with the
first irradiated region, thereby forming a second irradiated region and a non-irradiated region;

 wherein the second laser beam is irradiated to the thin-film to be coaxial with the first
laser beam;

 and wherein an alignment mark is formed by using an optical constant difference
between the second irradiated region and the non-irradiated region.
2. **(original)** The method according to claim 1, wherein the second laser beam is controlled
in such a way that the second irradiated region is solid.
3. **(currently amended)** The ~~met~~ method according to claim 1, wherein the second laser
beam is controlled in such a way that the second irradiated region is hollow due to ablation.
4. **(original)** The method according to claim 1, wherein the first irradiated region serves as
an annealed semiconductor region, in which an active region of a TFT is formed.
5. **(original)** The method according to claim 1, wherein the semiconductor thin-film is made
of a-Si (amorphous silicon).

6. **(original)** The method according to claim 1, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

7. **(original)** The method according to claim 1, wherein an excimer laser is used to generate the first laser beam.

8. **(original)** A method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region;

and

irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region or between the second irradiated region and a remaining non-irradiated region of the thin-film.

9. **(original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

10. **(original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

11. **(original)** The method according to claim 8, wherein the first irradiated region serves as a annealed semiconductor region, in which an active region of a TFT is formed.
12. **(original)** The method according to claim 8, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).
13. **(original)** The method according to claim 8, wherein the semiconductor thin-film is made of poly-Si film (polysilicon).
14. **(original)** The method according to claim 8, wherein an excimer laser is used to generate the first laser beam.
15. **(currently amended)** A [[The]] method of forming a semiconductor thin-film, comprising:
 - irradiating a first laser beam to a whole semiconductor thin-film to form a first irradiated region; and
 - irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;
 - wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;
 - and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region.

16. (original) The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

17. (original) The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

18. (original) The method according to claim 15, wherein the first irradiated region serves as an annealed semiconductor region, in which an active region of a TFT is formed.

19. (original) The method according to claim 15, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

20. (original) The method according to claim 15, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

21. (original) The method according to claim 15, wherein an excimer laser is used to generate the first laser beam.

22-26. (canceled)